

	Type	Hits	Search Text	DBs
1	BRS	971	438/14.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	3453	438/17.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	0	(generation adj rate near3 electron adj hole adj pairs) and volume adj integral	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	1	(generation adj rate near3 electron adj hole adj pairs) and volume	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	4	(generation adj rate near3 electron adj hole adj pairs) and ionization	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	433	438/140.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	13	generation adj rate near3 electron adj hole adj pairs	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	0	(generation adj rate near3 electron adj hole adj pairs) and threshold adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	13	(generation adj rate near3 electron adj hole adj pairs) and voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	0	(generation adj rate near3 electron adj hole adj pairs) and sapphire adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	48	insulated adj gate adj field adj effect adj transistor and sapphire adj substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	28	(insulated adj gate adj field adj effect adj transistor and sapphire adj substrate) and threshold adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	1	(generation adj rate near3 electron adj hole adj pairs) and electrical adj characteristics	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	33	time with variations with electrical adj characteristics	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	0	time with variations with electrical adj characteristics same driving adj current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	15622	driving adj current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp	Comments	Error Definition	Errors
1	2003/02/10 13:19			0
2	2003/02/10 13:13			0
3	2003/02/10 13:14			0
4	2003/02/10 13:23			0
5	2003/02/10 13:14			0
6	2003/02/10 13:19			0
7	2003/02/10 13:21			0
8	2003/02/10 13:36			0
9	2003/02/10 13:29			0
10	2003/02/10 13:25			0
11	2003/02/10 13:34			0
12	2003/02/10 13:27			0
13	2003/02/10 13:30			0
14	2003/02/10 13:45			0
15	2003/02/10 13:34			0
16	2003/02/10 13:34			0

	Type	Hits	Search Text	DBs
17	BRS	37	insulated adj gate adj field adj effect adj transistor and (driving adj current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	25	(insulated adj gate adj field adj effect adj transistor and (driving adj current)) and threshold adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	1	time with variations with electrical adj characteristics and (driving adj current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	6	insulated adj gate adj field adj effect adj transistor same (driving adj current)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	2	6195790.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	2	6051452.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	2	6304834.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	3	5889687.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Time Stamp	Comments	Error Definition	Errors
17	2003/02/10 13:45			0
18	2003/02/10 13:37			0
19	2003/02/10 13:45			0
20	2003/02/10 13:45			0
21	2003/02/10 13:59			0
22	2003/02/10 14:00			0
23	2003/02/10 14:01			0
24	2003/02/10 14:01			0